

Data Sheet

September 1998

File Number

2922.3

Quad, 3.5MHz, Operational Amplifier

HA-4741, which contains four amplifiers on a monolithic chip, provides a new measure of performance for general purpose operational amplifiers. Each amplifier in the HA-4741 has operating specifications that equal or exceed those of the 741-type amplifier in all categories of performance.

HA-4741 is well suited to applications requiring accurate signal processing by virtue of its low values of input offset voltage (0.5mV), input bias current (60nA) and input voltage noise (9nV/√Hz at 1kHz). 3.5MHz bandwidth, coupled with high open-loop gain, allow the HA-4741 to be used in designs requiring amplification of wide band signals, such as audio amplifiers. Audio application is further enhanced by the HA-4741's negligible output crossover distortion.

These excellent dynamic characteristics also make the HA-4741 ideal for a wide range of active filter designs. Performance integrity of multi-channel designs is assured by a high level of amplifier-to-amplifier isolation (69dB at 10kHz).

A wide range of supply voltages (±2V to ±20V) can be used to power the HA-4741, making it compatible with almost any system including battery-powered equipment.

HA-4741/883 product and data sheets available upon request.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.		
HA1-4741-2	-55 to 125	14 Ld CERDIP	F14.3		
HA1-4741-5	0 to 75	14 Ld CERDIP	F14.3		
HA3-4741-5	0 to 75	14 Ld PDIP	E14.3		
HA9P4741-9	-40 to 85	16 Ld SOIC	M16.3		

Features

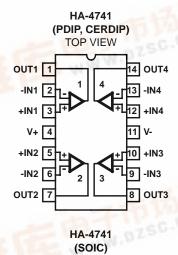
Slew Rate	
Bandwidth	3.5MHz
Input Voltage Noise	9nV/√ Hz
Input Offset Voltage	0.5mV
Input Bias Current	60nA
Supply Range	±2V to ±20V

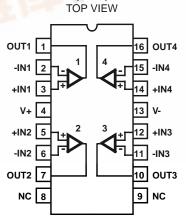
- · No Crossover Distortion
- Standard Quad Pinout

Applications

- Universal Active Filters
- D3 Communications Filters
- Audio Amplifiers
- Battery-Powered Equipment

Pinouts







Absolute Maximum Ratings

T _A = 25 ^o C Unless Otherwise Stated	
Supply Voltage Between V+ and V- Terminals	40V
Differential Input Voltage	30V
Input Voltage	PPLY
Output Short Circuit Duration (Note 3)	finite

Operating Conditions

Temperature Range:	
HA-4741-2	55°C to 125°C
HA-4741-5	0°C to 75°C
HA-4741-9	40°C to 85°C

Thermal Information

Thermal Resistance (Typical, Note 2)	θ _{JA} (°C/W)	θ _{JC} (^c C/W)
CERDIP Package	90	35
PDIP Package	107	N/A
SOIC Package	96	N/A
Maximum Junction Temperature (Ceramic Pa	ackage, Note 1	l)175 ⁰ C
Maximum Junction Temperature (Plastic Pac	kages, Note 1) 150 ⁰ C
Maximum Storage Temperature Range	65	^o C to 150°C
Maximum Lead Temperature (Soldering 1	0s)	300°C
(SOIC - Lead Tips Only)		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- Maximum power dissipation, including output load, must be designed to maintain junction temperature below 175°C for the ceramic package, and below 150°C for the plastic packages.
- 2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.
- 3. One amplifier may be shorted to ground indefinitely.

Electrical Specifications $V_{SUPPLY} = \pm 15V$, Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP.	HA-4741-2			HA-4741-5			(NOTE 4) HA-4741-9	
		(°C)	MIN	TYP	MAX	MIN	TYP	MAX	MAX	UNITS
INPUT CHARACTERISTICS		•					•			
Offset Voltage		25	-	0.5	3	-	1	5	5	mV
		Full	-	4	5	-	4	6.5	8.5	mV
Average Offset Voltage Drift		Full	-	5	-	-	5	-	-	μV/ ^o C
Bias Current		25	-	60	200	-	60	300	300	nA
		Full	-	-	325	-	-	400	400	nA
Offset Current		25	-	15	30	-	30	50	50	nA
		Full	-	-	75	-	-	100	100	nA
Common Mode Range		Full	±12	-	-	±12	-	-	-	V
Differential Input Resistance		25	-	0.5	-	-	0.5	-	-	МΩ
Input Voltage Noise	f = 1kHz	25	-	9	-	-	9	-	-	nV/√Hz
TRANSFER CHARACTERISTICS				1	I	I	·		1	
Large Signal Voltage Gain	$V_{OUT} = \pm 10V$,	25	50	100	-	25	50	-	-	kV/V
	$R_L = 2k\Omega$	Full	25	-	-	15	-	-	-	kV/V
Common Mode Rejection Ratio		25	80	95	-	80	95	-	-	dB
		Full	74	-	-	74	-	-	-	dB
Channel Separation (Note 5)		25	66	69	-	66	69	-	-	dB
Small Signal Bandwidth		25	2.5	3.5	-	2.5	3.5	-	-	MHz
OUTPUT CHARACTERISTICS				•		•		•		
Output Voltage Swing	$R_L = 10k\Omega$	Full	±12	±13.7	-	±12	±13.7	-	-	V
Output Voltage Swing	$R_L = 2k\Omega$	Full	±10	±12.5	-	±10	±12.5	-	-	V
Full Power Bandwidth (Notes 6, 7)		25	-	25	-	-	25	-	-	kHz
Output Current	$V_{OUT} = \pm 10V$	Full	±5	±15	-	±5	±15	-	-	mA
Output Resistance		25	-	300	-	-	300	-	-	Ω

Electrical Specifications $V_{SUPPLY} = \pm 15V$, Unless Otherwise Specified (Continued)

	TEST	TEMP.	H	IA-4741-	2	HA-4741-5		5	(NOTE 4) HA-4741-9	
PARAMETER	CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	MAX	UNITS
TRANSIENT RESPONSE $R_L = 2k\Omega$, $C_L = 50pF$										
Rise Time	V _{OUT} = ±200mV	25	-	75	140	-	75	140	140	ns
Overshoot		25	-	25	40	-	25	40	40	%
Slew Rate	V _{OUT} = ±5V	25	=	±1.6	-	-	±1.6	-	-	V/μs
POWER SUPPLY CHARACTERISTICS										
Supply Current		25	-	4.5	5	-	5	7	7	mA
Power Supply Rejection Ratio	$\Delta V_S = \pm 5V$	Full	80	95	=	80	95	-	-	dB

NOTES:

- 4. Typical and Minimum specifications for the -9 version are the same as those for the -5 version.
- 5. Referred to input; f = 10kHz, $R_S = 1k\Omega$, $V_{IN} = 100mV_{PEAK}$.
- 6. $V_{OUT} = \pm 10V$, $R_L = 2k\Omega$.
- 7. Full power bandwidth guaranteed based upon slew rate measurement: FPBW = S.R./ 2π V_{PEAK}.

Test Circuit and Waveforms

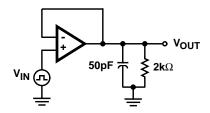


FIGURE 1. SMALL AND LARGE SIGNAL TEST CIRCUIT

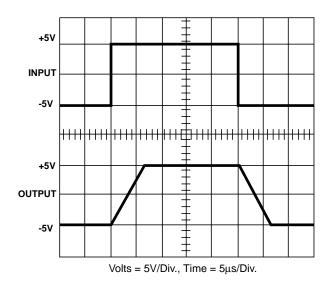
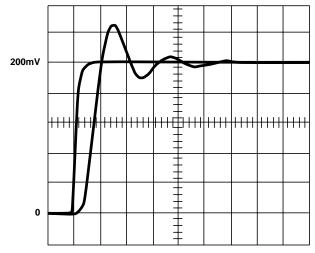


FIGURE 2. LARGE SIGNAL RESPONSE

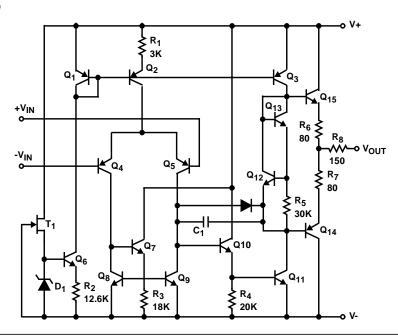


Volts = 40mV/Div., Time = 100ns/Div.

FIGURE 3. SMALL SIGNAL RESPONSE

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Schematic Diagram



Typical Performance Curves $V_{SUPPLY} = \pm 15V$, $T_A = 25^{\circ}C$, Unless Otherwise Specified

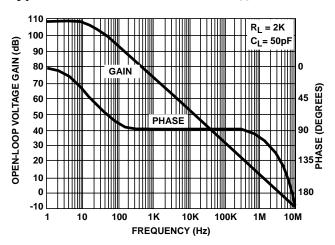


FIGURE 4. OPEN LOOP FREQUENCY RESPONSE

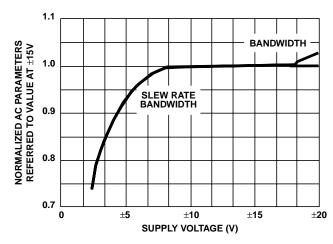


FIGURE 6. NORMALIZED AC PARAMETERS vs SUPPLY VOLTAGE

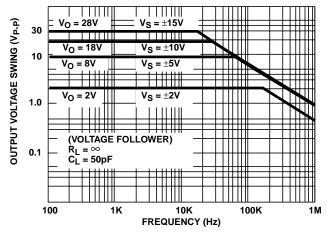


FIGURE 5. OUTPUT VOLTAGE SWING vs FREQUENCY

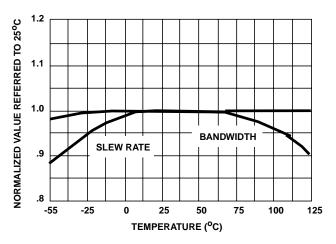


FIGURE 7. NORMALIZED AC PARAMETERS vs TEMPERATURE

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$\textit{Typical Performance Curves} \quad \text{V_{SUPPLY} = ± 15V, T_A = 25°C, Unless Otherwise Specified (Continued) and the support of the property of the$

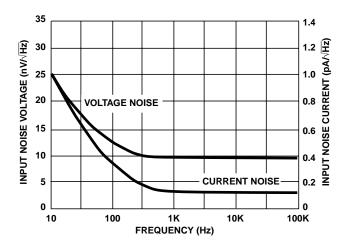


FIGURE 8. INPUT NOISE vs FREQUENCY

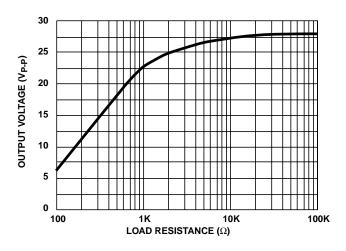


FIGURE 10. MAXIMUM OUTPUT VOLTAGE SWING vs LOAD RESISTANCE

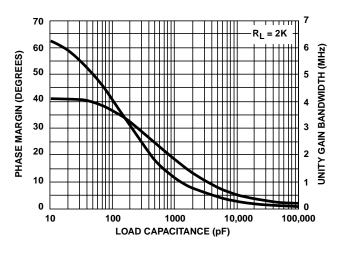


FIGURE 9. SMALL SIGNAL BANDWIDTH AND PHASE MARGIN vs LOAD CAPACITANCE

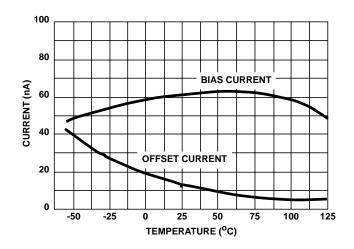


FIGURE 11. INPUT BIAS AND OFFSET CURRENT vs TEMPERATURE

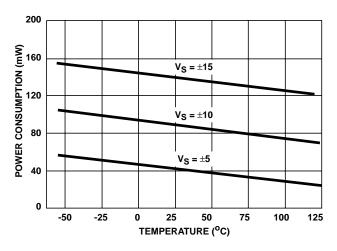


FIGURE 12. POWER CONSUMPTION vs TEMPERATURE

Die Characteristics

DIE DIMENSIONS:

87 mils x 75 mils x 19 mils 2210μm x 1910μm x 483μm

METALLIZATION:

Type: Al, 1% Cu Thickness: 16kÅ ±2kÅ

PASSIVATION:

Type: Nitride (Si₃N₄) over Silox (SiO₂, 5% Phos.)

Silox Thickness: 12kÅ ±2kÅ Nitride Thickness: 3.5kÅ ±1.5kÅ

SUBSTRATE POTENTIAL (Powered Up):

V-

TRANSISTOR COUNT:

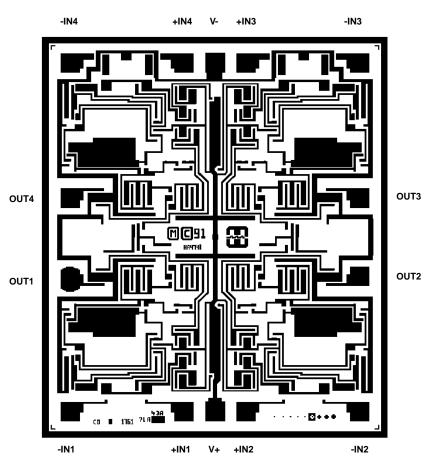
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PROCESS:

Junction Isolated Bipolar/JFET

Metallization Mask Layout

HA-4741



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